



20V Dual P-Channel MOSFETs

General Description

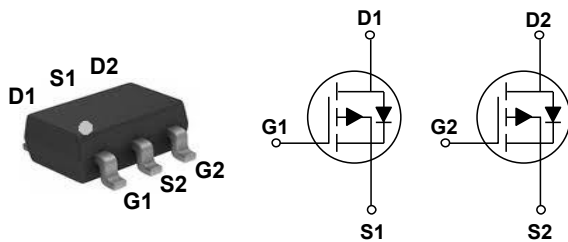
These dual P Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BV_{DSS}	R_{DS(ON)}	I_D
-20 V	85 mΩ	-3 A

Features

- R_{DS(ON)} ≤ 85mΩ @ V_{GS} = -4.5V
- Fast switching
- Green Device Available
- Suit for -1.8V Gate Drive Applications

SOT-23-6 Pin Configuration



Applications

- Notebook
- Hand-Held Instruments
- Load Switch

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	±10	V
I _D	Drain Current - Continuous (T _A =25°C)	-3	A
	Drain Current - Continuous (T _A =70°C)	-2.4	
I _{DM}	Drain Current - Pulsed (NOTE 1)	-12	A
P _D	Power Dissipation (T _A =25°C)	1.25	W
	Power Dissipation - Derate above 25°C	0.01	
T _J	Operating Junction Temperature Range	-55 to 150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
Marking Code		C	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to Ambient	---	100	°C/W



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Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V , I _D = -250uA	-20	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} = -20V , V _{GS} = 0V , T _J =25°C	---	---	-1	uA
		V _{DS} = -16V , V _{GS} = 0V , T _J =125°C	---	---	-10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±10V , V _{DS} = 0V	---	---	±100	nA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = -4.5V , I _D = -3A	---	70	85	mΩ
		V _{GS} = -2.5V , I _D = -2A	---	95	120	
		V _{GS} = -1.8V , I _D = -1A	---	130	170	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D = -250uA	-0.3	-0.6	-1.0	V
gfs	Forward Transconductance	V _{DS} = -10V , I _S = -1A	---	2.2	---	S

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q _g	Total Gate Charge	V _{DS} = -10V , V _{GS} = -4.5V , I _D = -3A (NOTE 2、3)	---	4.8	8	nC
Q _{gs}	Gate-Source Charge		---	0.5	1	
Q _{gd}	Gate-Drain Charge		---	1.9	4	
T _{d(on)}	Turn-On Delay Time	V _{DD} = -10V , V _{GS} = -4.5V , R _G =25Ω , I _D = -1A (NOTE 2、3)	---	3.5	7	nS
T _r	Rise Time		---	12.6	24	
T _{d(off)}	Turn-Off Delay Time		---	32.6	62	
T _f	Fall Time		---	8.4	16	
C _{iss}	Input Capacitance	V _{DS} = -15V , V _{GS} = 0V , F= 1MHz	---	350	510	pF
C _{oss}	Output Capacitance		---	65	95	
C _{rss}	Reverse Transfer Capacitance		---	50	75	

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G = V _D = 0V , Force Current	---	---	-3	A
I _{SM}	Pulsed Source Current		---	---	-6	A
V _{SD}	Diode Forward Voltage	V _{GS} = 0V , I _S = -1A , T _J = 25°C	---	---	-1	V

NOTES :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
3. Essentially independent of operating temperature.



Characteristics Curves

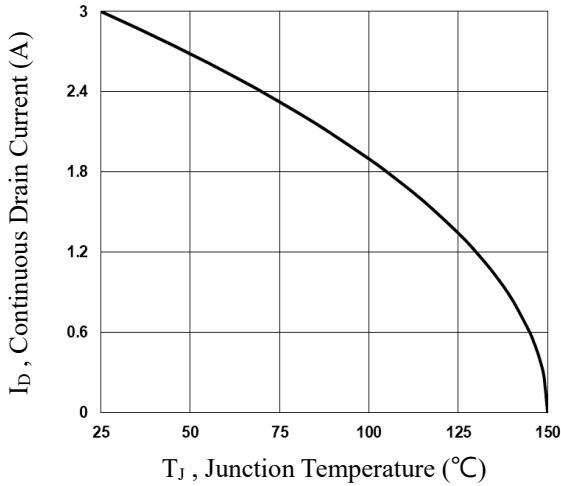


Fig.1 Continuous Drain Current vs. T_J

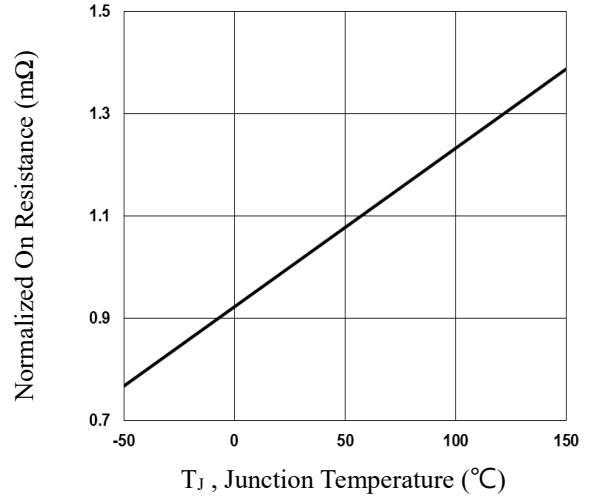


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

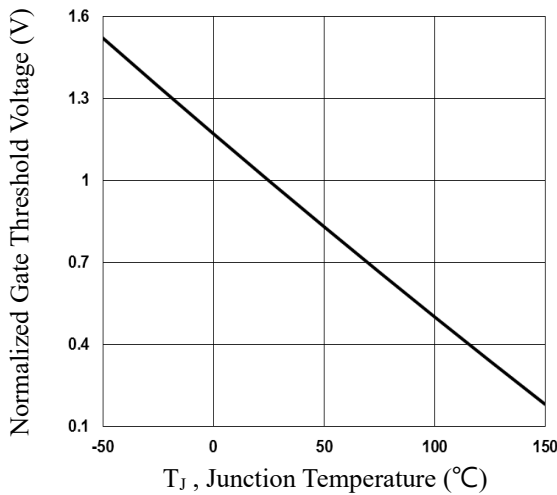


Fig.3 Normalized V_{th} vs. T_J

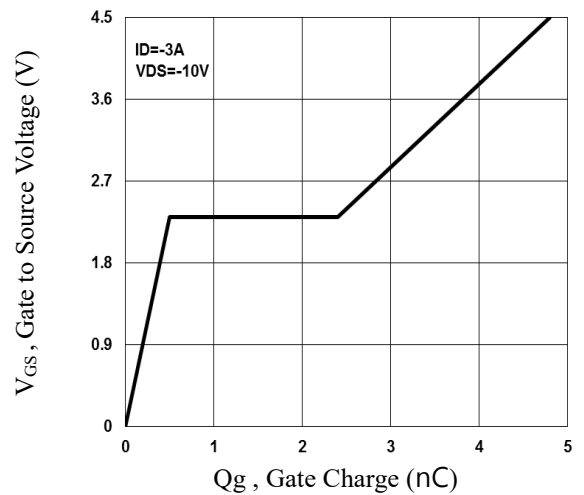


Fig.4 Gate Charge Waveform

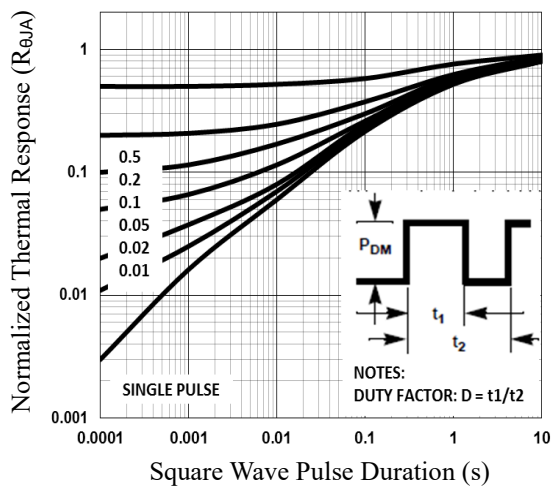


Fig.5 Normalized Transient Impedance

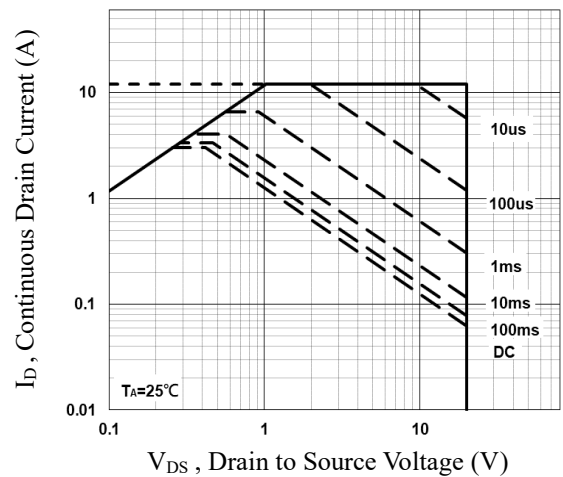


Fig.6 Maximum Safe Operation Area



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Characteristics Curves

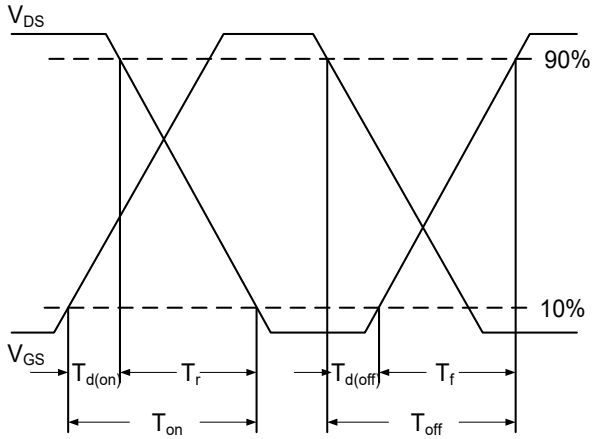


Fig.7 Switching Time Waveform

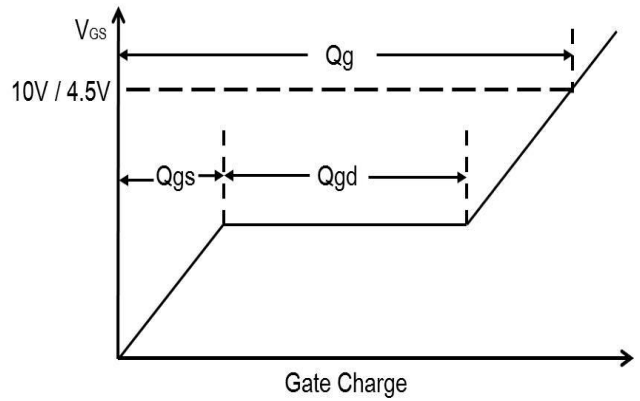
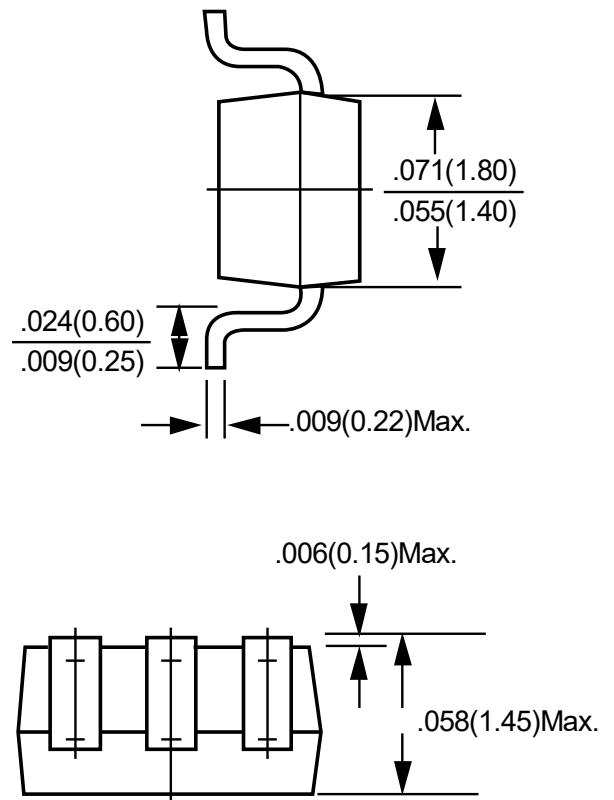
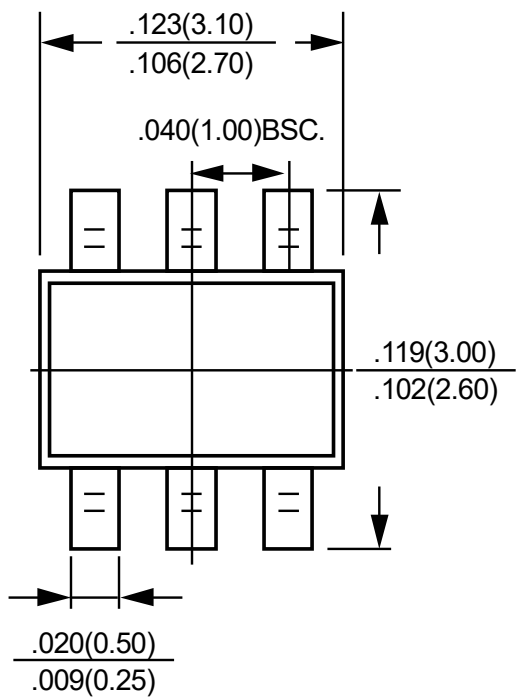


Fig.8 Gate Charge Waveform

Package Outline Dimensions



SOT-23-6

Dimensions in inches and (millimeters)



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